



# 60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-16 A

### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}$ @-10V, $I_D$ @-8A<48m $\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@-4.5V$ , $I_D@-4A<65m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

### **Mechanical Data**

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams
- Marking: Q5465A

# DFN5060-8L

# Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	-60	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	-16		
	T <sub>C</sub> =100°C		-10	Α	
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	-64		
Power Dissipation	T <sub>C</sub> =25°C	Po	25	14/	
	T <sub>C</sub> =100°C		10	W	
Continuous Drain Current	T <sub>A</sub> =25°C	I <sub>D</sub>	-5.0	Α	
	T <sub>A</sub> =70°C		-4.0	А	
Power Dissipation	T <sub>A</sub> =25°C		2.0	W	
Power Dissipation	T <sub>A</sub> =70°C	Po	1.3		
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	51	mJ	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	5.0	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250$ uA	-1.0	-1.7	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V,I <sub>D</sub> =-8A	-	40	48	mΩ
		$V_{GS}$ =-4.5V, $I_{D}$ =-4A	-	55	65	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-60V, $V_{GS}$ =0V	-	-	-1.0	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	$Q_g$	$V_{DS}$ =-30V, $I_{D}$ =-8A, $V_{GS}$ =-10V (Note 3)	-	22	-	nC
Gate-Source Charge	$Q_gs$		-	4.1	-	
Gate-Drain Charge	$Q_gd$		-	5.2	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, f=1.0MHZ	-	1256	-	pF
Output Capacitance	Coss		-	87	-	
Reverse Transfer Capacitance	Crss	I=1.0IVINZ	-	59	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	13	-	ns
Turn-On Rise Time	t <sub>r</sub>	$V_{DD}$ =-30V, $I_{D}$ =-1A, $V_{GS}$ =-10V, $R_{G}$ =6 $\Omega$ (Note 3)	-	42	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	65	-	
Turn-Off Fall Time	t <sub>f</sub>		-	16	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	I.		-	-	-16	А
Diode Forward Current	I <sub>S</sub>					
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A,V <sub>GS</sub> =0V	-	-0.72	-1.0	V

### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. R<sub>OJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =32A,  $V_{DD}$ =25V,  $V_{GS}$ =10V
- 7. Guaranteed by design, not subject to production testing.





### **TYPICAL CHARACTERISTIC CURVES**

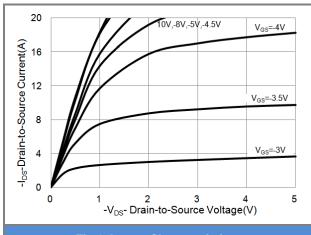
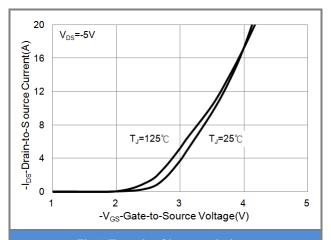


Fig.1 Output Characteristics



**Fig.2 Transfer Characteristics** 

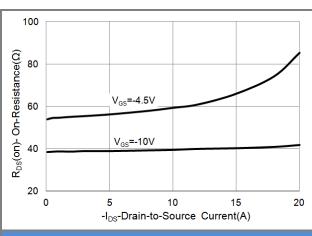


Fig.3 On-Resistance vs. Drain Current

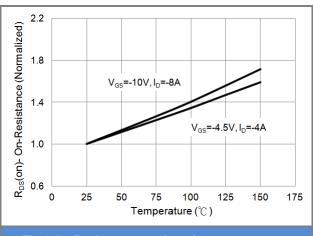


Fig.4 On-Resistance vs. Junction temperature

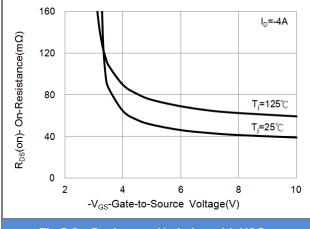


Fig.5 On-Resistance Variation with VGS.

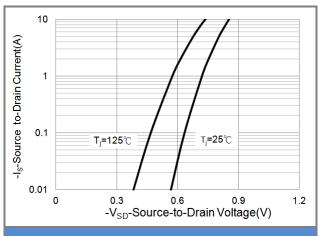


Fig.6 Source-Drain Diode Forward Voltage





### TYPICAL CHARACTERISTIC CURVES

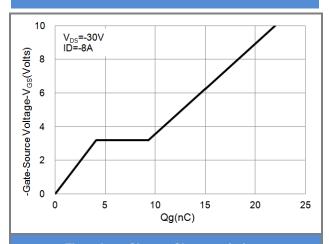


Fig.7 Gate-Charge Characteristics

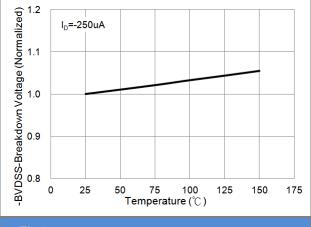


Fig.8 Breakdown Voltage Variation vs. Temperature

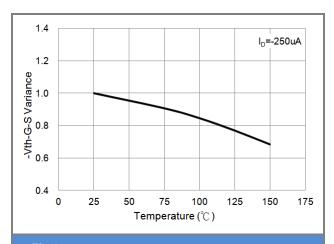


Fig.9 Threshold Voltage Variation with Temperature

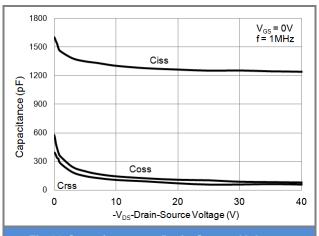
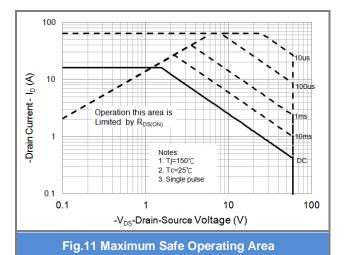


Fig.10 Capacitance vs. Drain-Source Voltage







### **TYPICAL CHARACTERISTIC CURVES**

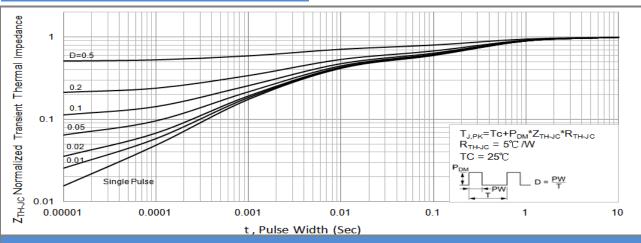


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

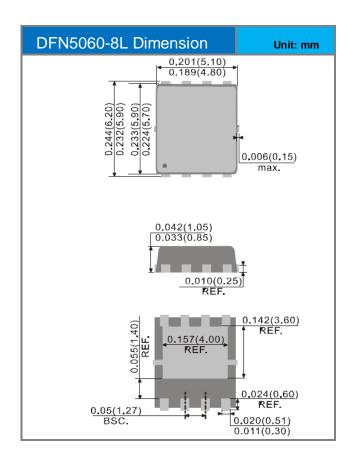


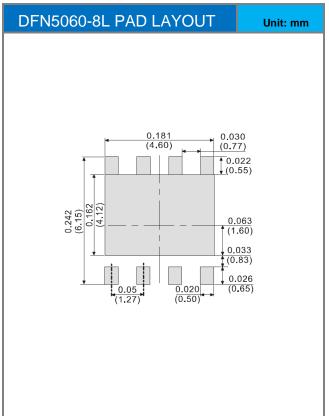


### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Packing type Marking	
PJQ5465A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5465A	Halogen free

## **Packaging Information & Mounting Pad Layout**









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